

Discussion on Defect and Material Characterization

- Differences between n- and p-type materials (FZ, MCZ, EPI)
Which resistivity would be needed for the p-type samples ($5e12$ - $5e13\text{cm}^{-3}$)
- Elena: Check on literature e.g. GADEST to see if we missed information provided by solid state physics community. Investigate lifetime data from Vilnius – correlations with measured defects.
- Pawel: Fluence dependence of defect generation
- Samples for defect characterization: Do we need more or other type of samples? No, we seem to have enough samples.
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- **Defects responsible for trapping? How to characterize?**
Photoconductivity measurements in Vilnius – need irradiated silicon pieces / wafers
- How reliable are the measurements of the defect concentrations as measured by different methods?
- Inter correlation of the various defect characterization methods used within RD50!